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TVS Diode Arrays (SPA®Diodes) Lightning Surge Protection - SP2555NUTG

SP2555NUTG 2.5V 45A Diode Array



Pinout



Functional Block Diagram



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

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Description

The SP2555NUTG is a low-capacitance, TVS Diode Array designed to provide protection against ESD (electrostatic discharge), CDE (cable discharge events), EFT (electrical fast transients), and lightning induced surges for highspeed, differential data lines. It's packaged in a µDFN package (3.0 x 2.0mm) and each device can protect up 4 channels or 2 differential pairs, up to 45A (IEC 61000-4-5 2nd edition,) and up to 30kV ESD (IEC 61000-4-2). The "flow-through" design minimizes signal distortion, reduces voltage overshoot, and provides a simplified PCB design.

The SP2555NUTG with its low capacitance and low clamping voltage makes it ideal for high-speed data interfaces such as 1GbE applications found in notebooks, switches, etc.

Features

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, IEC 61000-4-5 2nd edition, 45A $(t_{p}=8/20\mu s)$
- · Low capacitance of 2.5pF@0V (TYP) per I/O
- Low leakage current of 0.1µA (TYP) at 2.5V

• µDFN-10 package is optimized for high-speed data line routing

F RoHS (PG) GREEN

- · Provides protection for two differential data pairs (4 channels) up to 45A
- Low operating and clamping voltage
- AEC-Q101 gualified
- Halogen free, Lead free and RoHS compliant

Applications

- •10/100/1000 Ethernet • WAN/LAN Equipment
- LVDS Interfaces

• Smart TV

- Integrated Magnetics
- Desktops, Servers and Notebooks

Application Example



SP2555

Absolute Maximum Ratings

Symbol	Parameter	Value	Units	
I _{pp}	Peak Current (t _p =8/20µs)	45	А	
P _{Pk}	Peak Pulse Power (t _p =8/20µs)	1000	W	
T _{op}	Operating Temperature	-40 to 125	°C	
T _{STOR}	Storage Temperature	-55 to 150	°C	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1µA			2.5	V
Reverse Leakage Current	I _R	V _{RWM} = 2.5V, T = 25°C		0.1	0.5	μA
Snap Back Voltage	V _{SB}	I _{SB} = 50mA	2.0			V
		$I_{pp} = 1A$, $t_p = 8/20\mu s$, Any I/O to Ground		4.5		
		$I_{\rm PP}$ = 10A, t _p = 8/20µs, Any I/O to Ground		7.5		V
Clamp Voltage	V _c	$I_{\rm PP}$ = 25A, t _p = 8/20µs, Any I/O to Ground		12		
		$I_{pp} = 45A$, $t_p = 8/20\mu$ s, Line-to-Line ¹ , two I/O Pins connected together on each line		19		
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Any I/O to Ground		0.1		Ω
ESD Withstand Valtage		IEC 61000-4-2 (Contact)	±30			kV
ESD Withstand Voltage	V _{ESD}	IEC 61000-4-2 (Air)	±30			Ω kV kV
Diode Capacitance	C _{I/O to GND}	Between I/O Pins and Ground V _R = 0V, f = 1MHz		2.5		pF
	C _{I/O to I/O}	Between I/O Pins V _R = 0V, f = 1MHz		1.2		pF

Notes:

1. Rating with 2 pins connected together per sugguested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6)

2. Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2= 90ns





Clamping Voltage vs. I_{PP} (Line-to-Line)



TLP Current (A) TLP Voltage (V)

Transmission Line Pulsing(TLP) Plot

Clamping Voltage vs. I_{PP} (I/O to GND)



8/20µS Pulse Waveform





TVS Diode Arrays (SPA®Diodes) Lightning Surge Protection - SP2555NUTG

Soldering Parameters

Reflow Cor	ndition	Pb – Free assembly	
	-Temperature Min (T _{s(min)})	150°C	
Pre Heat	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 180 secs	
Average rai to peak	mp up rate (Liquidus) Temp (T_L)	3°C/second max	
${\sf T}_{\rm S(max)}$ to ${\sf T}_{\rm L}$	- Ramp-up Rate	3°C/second max	
Poflow	-Temperature (T _L) (Liquidus)	217°C	
nellow	-Temperature (t _L)	60 – 150 seconds	
Peak Temp	erature (T _P)	260 ^{+0/-5} °C	
Time within Temperatur	n 5°C of actual peak re (t _p)	20 – 40 seconds	
Ramp-dow	n Rate	6°C/second max	
Time 25°C	to peak Temperature (T _P)	8 minutes Max.	
Do not exc	eed	260°C	



Ordering Information

Part Number	Package	Marking	Min. Order Qty.
SP2555NUTG	µDFN-10 (3.0x2.0mm)	SP2555	3000

Part Numbering System



Part Marking System





TVS Diode Arrays (SPA®Diodes) Lightning Surge Protection - SP2555NUTG

Package Dimensions – µDFN-10 (3.0x2.0mm)





	1	0.95r	nm0	.95mm	<u>0</u> .	<u>25mm</u>
	Ø			Ø		
U.85mm		_				1.40mm
			Ð	₿		0.60mm
	<u>p</u> .60	mm_0.6	5mm_0.6	5mm 0.6	Omm	

Recommended Stencil Apertures
Recommended Otenen Apertares
Recommended Stencil thickness 5mils

Package	µDFN-10 (3.0x2.0mm)					
JEDEC			MO-2	229		
Symbol	Millimeters		Inches			
Symbol	Min	Nom	Max	Min	Nom	Max
Α	0.50	0.60	0.65	0.020	0.024	0.026
A1	0.00	0.03	0.05	0.000	0.001	0.002
A3	0.15 Ref			0.006 Ref		
b	0.15	0.20	0.25	0.006	0.008	0.010
b1	0.25	0.35	0.45	0.010	0.014	0.018
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.90	2.00	2.10	0.075	0.079	0.083
е	0.60 BSC 0.024 BSC					
e1	0.65 BSC 0.026 BSC					
e2	0.95 BSC				0.037	
L	0.25	0.30	0.35	0.010	0.012	0.014
L1	0.95	1.00	1.05	0.037	0.039	0.041

Notes :

1. All dimensions are in millimeters

2. Dimensions include solder plating.

3. Dimensions are exclusive of mold flash & metal burr.

4. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.

5. Package surface matte finish VDI 11-13.

PO P2 | ø1.55±0.05 **Device Orientation in Tape** T→ Ε (+)Тор **A**0 -Cover F W Tape \oplus B0 \oplus \bigoplus 5° Max Pin1 Location ø1.0±0.1 KO Ρ

Package	µDFN-10 (3.0x2.0mm)
Symbol	Millimeters
A0	2.30 +/- 0.10
B0	3.20 +/- 0.10
E	1.75 +/- 0.10
F	3.50 +/- 0.05
K0	1.0 +/- 0.10
Р	4.00 +/- 0.10
P0	4.00 +/- 0.10
P2	2.00 +/- 0.10
т	0.3 +/- 0.05
W	8.00 +0.30/- 0.10

Tape & Reel Specification – µDFN-10 (3.0x2.0mm)